

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
- 30	0.012 at V _{GS} = - 10 V	- 8.8
	0.019 at V _{GS} = - 4.5 V	- 7.0

FEATURES

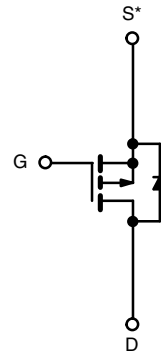
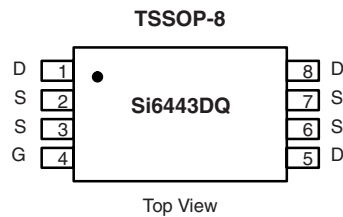
- Halogen-free
- TrenchFET[®] Power MOSFET



RoHS
COMPLIANT

APPLICATIONS

- Battery Switch
- Load Switch



* Source Pins 2, 3, 6 and 7 must be tied common.

Ordering Information: Si6443DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 30		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 8.8	- 7.3	A
		T _A = 70 °C	- 7.2	- 5.9	
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	- 30			
Continuous Source Current (Diode Conduction) ^a	I _S	- 1.35	- 0.95		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	1.50	1.05	W
		T _A = 70 °C	1.0	0.67	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	60	83	°C/W
	Steady State		100	120	
Maximum Junction-to-Foot	Steady State	R _{thJF}	35	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



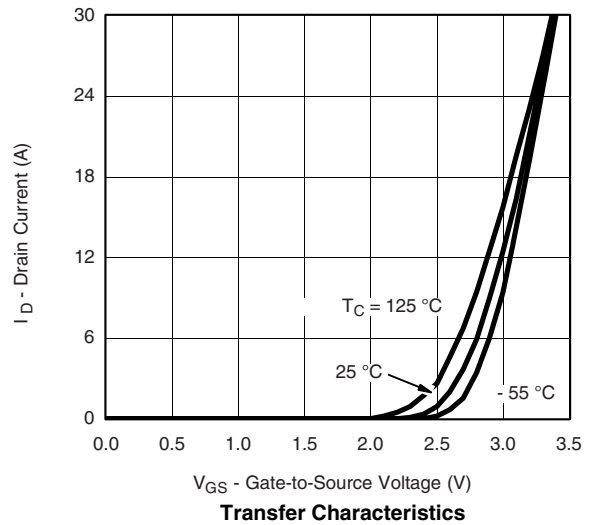
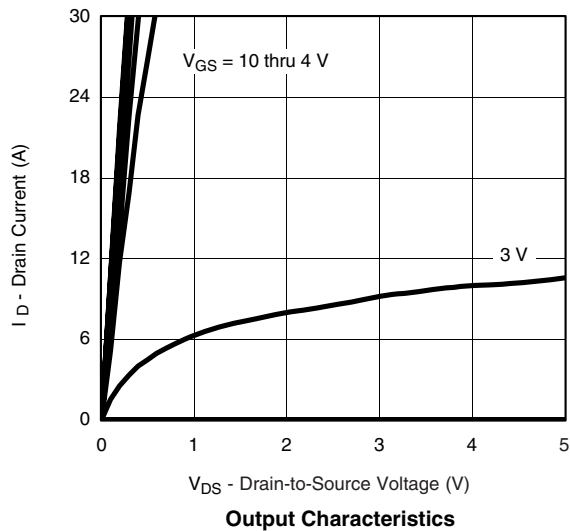
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -8.8\text{ A}$		0.0095	0.012	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -7.2\text{ A}$		0.0145	0.019	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -8.8\text{ A}$		30		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.5\text{ A}, V_{GS} = 0\text{ V}$		-0.71	-1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -5\text{ V}, I_D = -8.8\text{ A}$		38	60	nC
Gate-Source Charge	Q_{gs}		9.3			
Gate-Drain Charge	Q_{gd}		17.7			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_G = 6\text{ }\Omega$		25	40	ns
Rise Time	t_r		21	35		
Turn-Off Delay Time	$t_{d(off)}$		115	180		
Fall Time	t_f		68	110		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		65	100	

Notes:

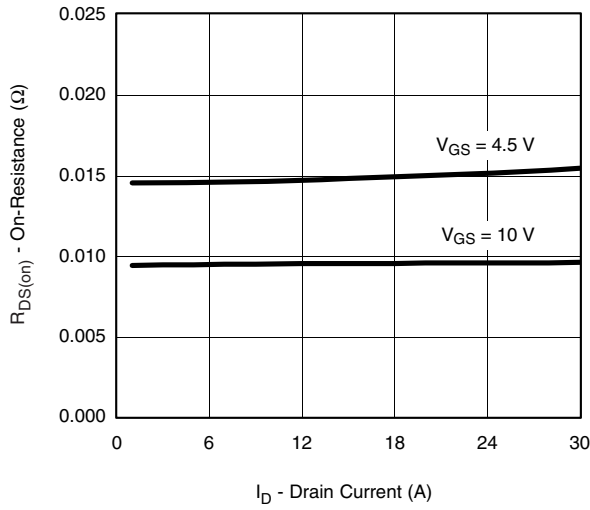
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

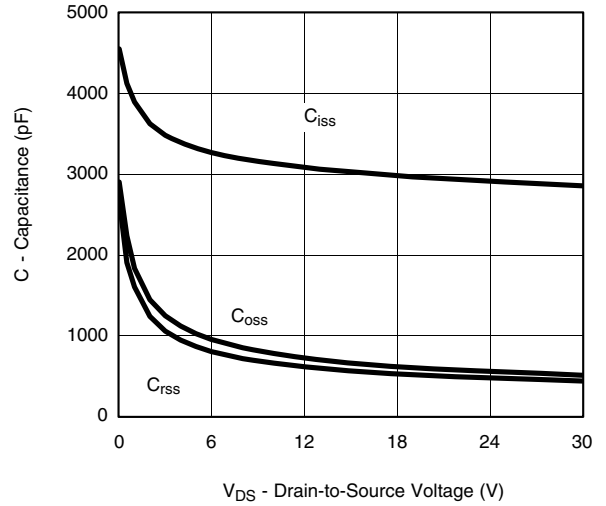
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



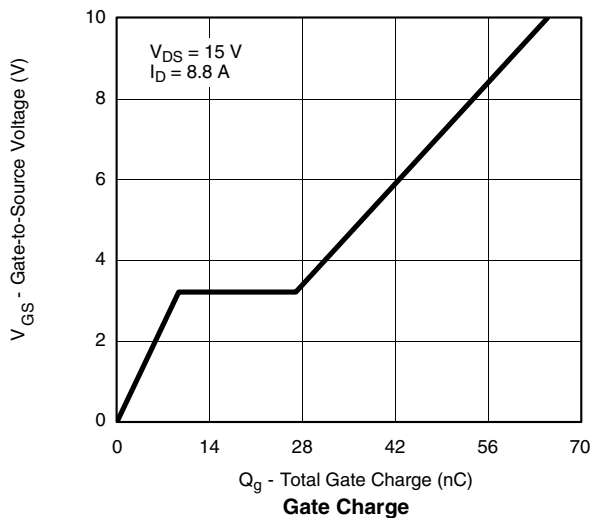
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



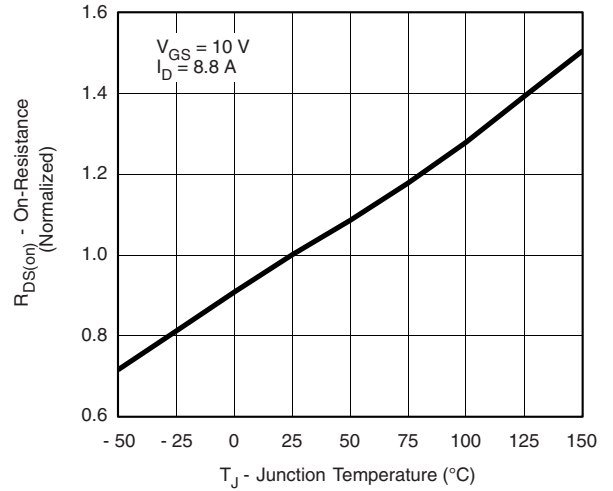
On-Resistance vs. Drain Current



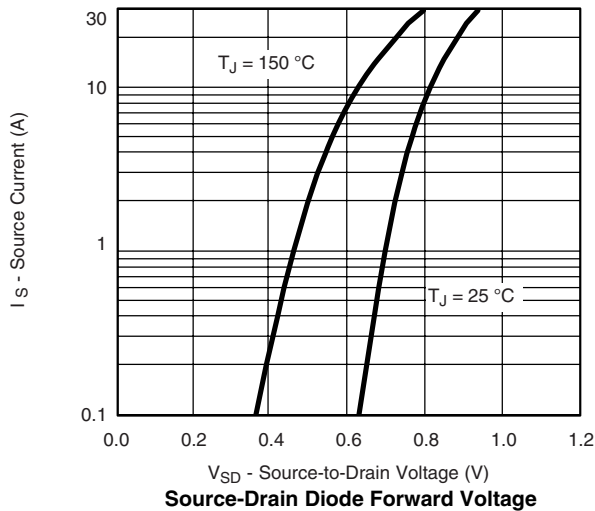
Capacitance



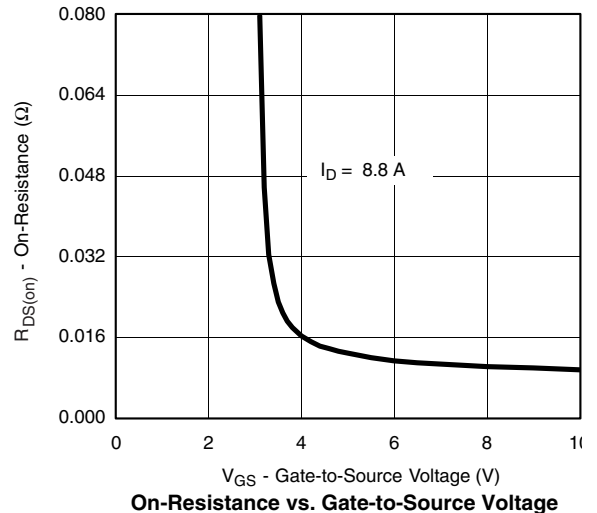
Gate Charge



On-Resistance vs. Junction Temperature

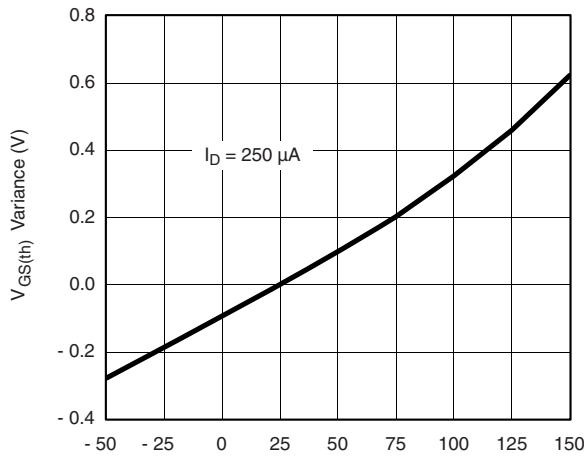


Source-Drain Diode Forward Voltage

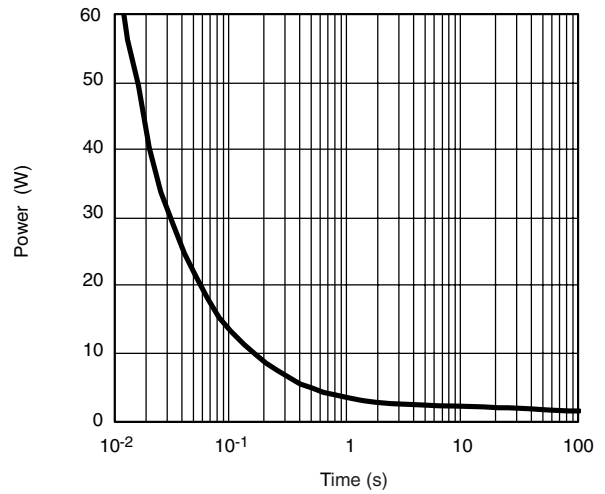


On-Resistance vs. Gate-to-Source Voltage

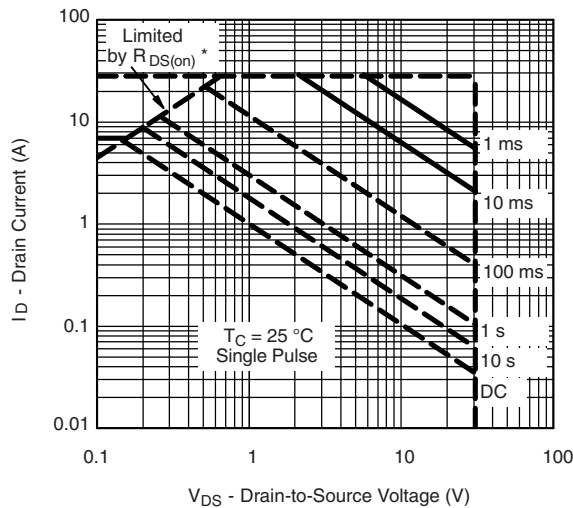
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Threshold Voltage

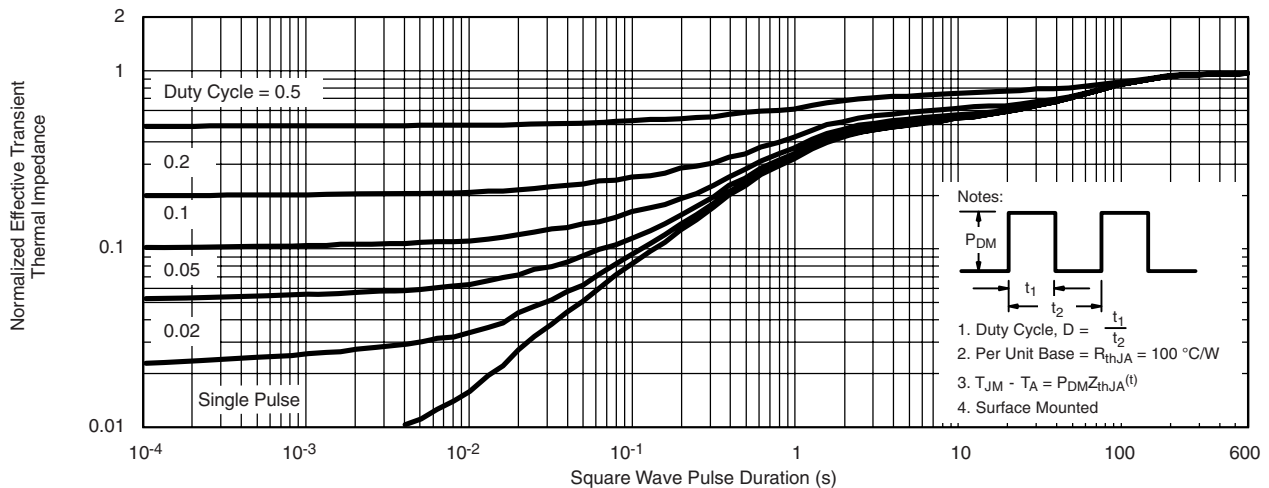


Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

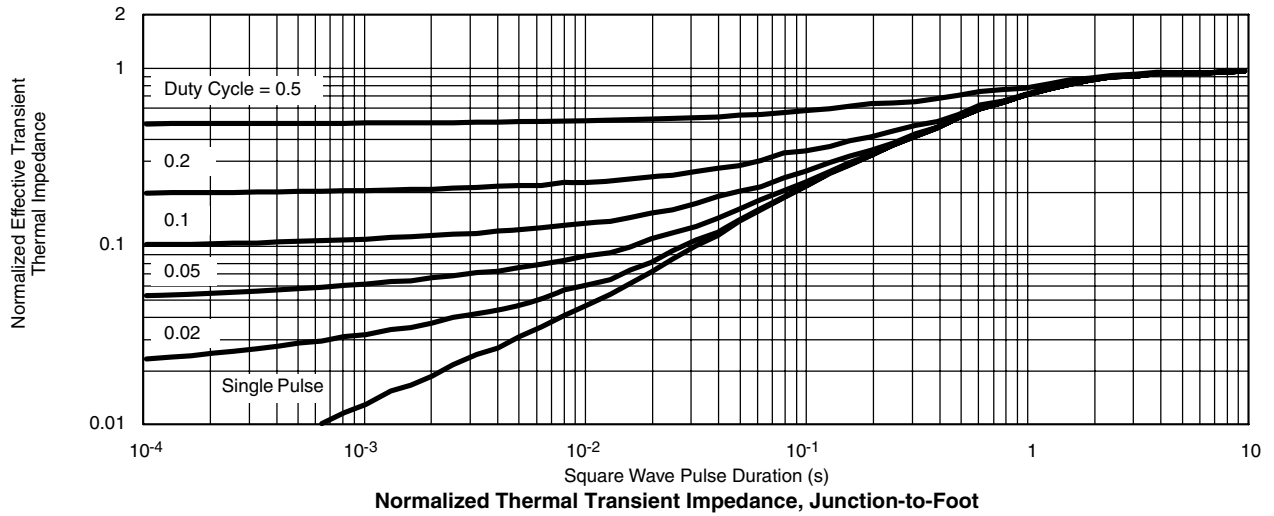
Safe Operating Area, Junction-to-Case



- Notes:
- Duty Cycle, $D = \frac{t_1}{t_1 + t_2}$
 - Per Unit Base = $R_{thJA} = 100 \text{ } ^\circ\text{C/W}$
 - $T_{JM} - T_A = P_{DM}Z_{thJA}(t)$
 - Surface Mounted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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